

REPETITIVE AVALANCHE AND dv/dt RATED HEXFET® TRANSISTOR

IRHM9064

P-CHANNEL RAD HARD

-60 Volt, 0.060Ω, RAD HARD HEXFET

International Rectifier's P-Channel RAD HARD technology HEXFETs demonstrate excellent threshold voltage stability and breakdown voltage stability at total radiation doses as high as 10^5 Rads (Si). Under **identical** pre- and post-radiation test conditions, International Rectifier's P-Channel RAD HARD HEXFETs retain **identical** electrical specifications up to 1×10^5 Rads (Si) total dose. No compensation in gate drive circuitry is required. These devices are also capable of surviving transient ionization pulses as high as 1×10^{12} Rads (Si)/Sec, and return to normal operation within a few micro-seconds. Single Event Effect (SEE) testing of International Rectifier P-Channel RAD HARD HEXFETs has demonstrated virtual immunity to SEE failure. Since the P-Channel RAD HARD process utilizes International Rectifier's patented HEXFET technology, the user can expect the highest quality and reliability in the industry.

P-Channel RAD HARD HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high-energy pulse circuits in space and weapons environments.

Absolute Maximum Ratings

	Parameter	IRHM9064	Units
I_D @ $V_{GS} = -12V, T_C = 25^\circ C$	Continuous Drain Current	-35*	A
I_D @ $V_{GS} = -12V, T_C = 100^\circ C$	Continuous Drain Current	-26	
I_{DM}	Pulsed Drain Current ①	-168	
P_D @ $T_C = 25^\circ C$	Max. Power Dissipation	250	W
	Linear Derating Factor	2.0	W/K ⑤
V_{GS}	Gate-to-Source Voltage	± 20	V
EAS	Single Pulse Avalanche Energy ②	500	mJ
I_{AR}	Avalanche Current ①	-35*	A
EAR	Repetitive Avalanche Energy ①	25	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.5	V/ns
T_J	Operating Junction	-55 to 150	
T_{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s	$^\circ C$
	Weight	9.3 (typical)	g

Product Summary

Part Number	BV_{DSS}	$R_{DS(on)}$	I_D
IRHM9064	-60V	0.060Ω	-35*A

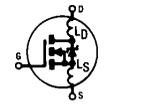
Features:

- Radiation Hardened up to 1×10^5 Rads (Si)
- Single Event Burnout (SEB) Hardened
- Single Event Gate Rupture (SEGR) Hardened
- Gamma Dot (Flash X-Ray) Hardened
- Neutron Tolerant
- Identical Pre- and Post-Electrical Test Conditions
- Repetitive Avalanche Rating
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Electrically Isolated
- Ceramic Eyelets

Pre-Radiation

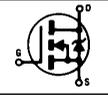
Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	-60	—	—	V	V _{GS} = 0 V, I _D = -1.0mA
ΔBV _{DSS} /ΔT _J	Temperature Coefficient of Breakdown Voltage	—	-0.048	—	V/°C	Reference to 25°C, I _D = -1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.060 0.070	Ω	V _{GS} = -12V, I _D = -26A ④ V _{GS} = -12V, I _D = -35A
V _{GS(th)}	Gate Threshold Voltage	-2.0	—	-4.0	V	V _{DS} = V _{GS} , I _D = -1.0mA
g _{fs}	Forward Transconductance	16	—	—	S (τ)	V _{DS} > -15V, I _{DS} = -26 A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	-25 -250	μA	V _{DS} = 0.8 x Max Rating, V _{GS} = 0V V _{DS} = 0.8 x Max Rating V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V _{GS} = -20 V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	100	nA	V _{GS} = 20V
Q _g	Total Gate Charge	—	—	260	nC	V _{GS} = -12V, I _D = -35A V _{DS} = Max Rating x 0.5
Q _{gs}	Gate-to-Source Charge	—	—	60		
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	86		
t _{d(on)}	Turn-On Delay Time	—	—	62	ns	V _{DD} = -30V, I _D = -35A, R _G = 2.35Ω
t _r	Rise Time	—	—	227		
t _{d(off)}	Turn-Off Delay Time	—	—	200		
t _f	Fall Time	—	—	115		
L _D	Internal Drain Inductance	—	8.7	—	nH	Measured from drain lead, 6mm (0.25 in) from package to center of die. Modified MOSFET symbol showing the internal inductances.
L _S	Internal Source Inductance	—	8.7	—		
C _{iss}	Input Capacitance	—	7400	—	pF	V _{GS} = 0V, V _{DS} = -25 V f = 1.0MHz
C _{oss}	Output Capacitance	—	3200	—		
C _{rss}	Reverse Transfer Capacitance	—	540	—		



Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-35	A	Modified MOSFET symbol showing the integral reverse p-n junction rectifier.
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	-168		
V _{SD}	Diode Forward Voltage	—	—	-3.0	V	T _J = 25°C, I _S = -35A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	480	ns	T _J = 25°C, I _F = -35A, di/dt ≤ -100A/μs
Q _{RR}	Reverse Recovery Charge	—	—	3.7	μC	V _{DD} ≤ -50V ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				



Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	0.50	K/W ⑤	Typical socket mount
R _{thJA}	Junction-to-Ambient	—	—	48		
R _{thCS}	Junction-to-Sink	—	0.21	—		

Radiation Performance of P-Channel Rad Hard HEXFETs

International Rectifier Radiation Hardened HEXFETs are tested to verify their hardness capability. The hardness assurance program at International Rectifier uses two radiation environments.

Every manufacturing lot is tested in a low dose rate (total dose) environment per MIL-STD-750, test method 1019. International Rectifier has imposed a standard gate voltage of -12 volts per note 6 and a V_{DSS} bias condition equal to 80% of the device rated voltage per note 7. Pre- and post-radiation limits of the devices irradiated to 1×10^5 Rads (Si) are identical and are presented in Table 1. The values in Table 1 will be met for either of the two low dose rate test

circuits that are used. Both pre- and post-radiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison. It should be noted that at a radiation level of 1×10^5 Rads (Si) no changes in limits are specified in DC parameters.

High dose rate testing may be done on a special request basis using a dose rate up to 1×10^{12} Rads (Si)/Sec.

International Rectifier radiation hardened P-Channel HEXFETs are considered to be neutron-tolerant, as stated in MIL-PRF-19500 Group D. International Rectifier radiation hardened P-Channel HEXFETs have been characterized in heavy ion Single Event Effects (SEE) environments and the results are shown in Table 3.

Table 1. Low Dose Rate ⑥ ⑦

		IRHM9064			
Parameter	Description	100K Rads (Si)		Units	Test Conditions ⑩
		Min	Max		
BV_{DSS}	Drain-to-Source Breakdown Voltage	-200	—	V	$V_{GS} = 0V, I_D = -1.0mA$
$V_{GS(th)}$	Gate Threshold Voltage ④	-2.0	-4.0		$V_{GS} = V_{DS}, I_D = -1.0mA$
I_{GSS}	Gate-to-Source Leakage Forward	—	-100	nA	$V_{GS} = -20V$
I_{GSS}	Gate-to-Source Leakage Reverse	—	100		$V_{GS} = 20V$
I_{DSS}	Zero Gate Voltage Drain Current	—	-25	μA	$V_{DS}=0.8 \times \text{Max Rating}, V_{GS}=0V$
$R_{DS(on)1}$	Static Drain-to-Source On-State Resistance One ④	—	0.060	Ω	$V_{GS} = -12V, I_D = -26A$
V_{SD}	Diode Forward Voltage ④	—	-3.0	V	$TC = 25^\circ C, I_S = -35A, V_{GS} = 0V$

Table 2. High Dose Rate ⑧

Parameter	Description	10^{11} Rads (Si)/sec			10^{12} Rads (Si)/sec			Units	Test Conditions
		Min	Typ	Max	Min	Typ	Max		
V_{DSS}	Drain-to-Source Voltage	—	—	-48	—	—	-48	V	Applied drain-to-source voltage during gamma-dot
IPP	Peak radiation induced photo-current	—	-100	—	—	-100	—	A	
di/dt	Rate of rise of photo-current	—	-800	—	—	-160	—	A/ μ sec	
L_1	Circuit inductance required to limit di/dt	0.1	—	—	0.8	—	—	μH	

Table 3. Single Event Effects ⑨

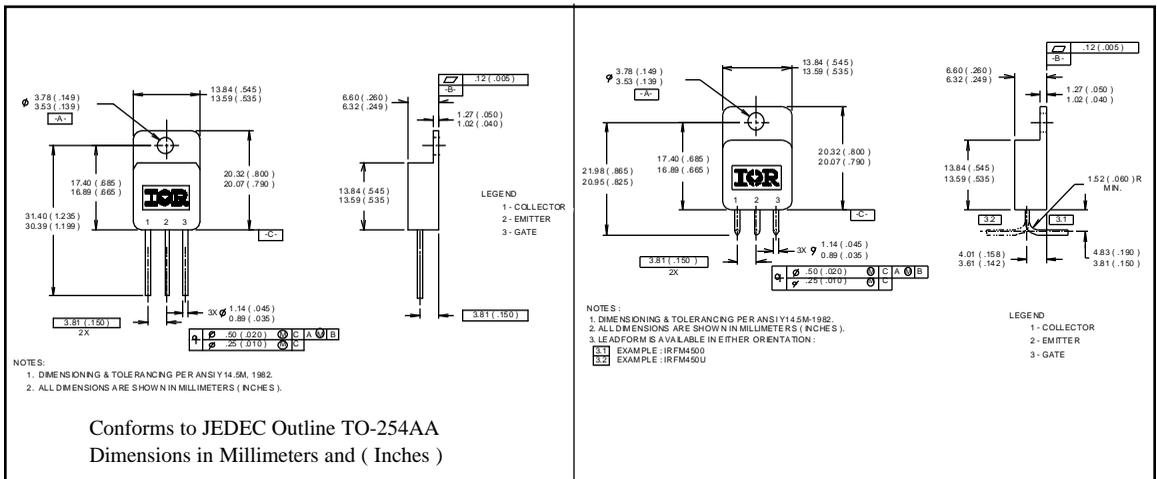
Parameter	Typical	Units	Ion	LET (Si) (MeV/mg/cm ²)	Fluence (ions/cm ²)	Range (μm)	V_{DS} Bias (V)	V_{GS} Bias (V)
BV_{DSS}	-60	V	Ni	28	1×10^5	~41	-60	5

- ① Repetitive Rating; Pulse width limited by maximum junction temperature. Refer to current HEXFET reliability report.
- ② @ $V_{DD} = -25V$, Starting $T_J = 25^\circ C$,
 $E_{AS} = [0.5 * L * (I_L^2) * (BV_{DSS}/(BV_{DSS}-V_{DD}))]$
 Peak $I_L = -35A$, $V_{GS} = -12V$, $25 \leq R_G \leq 200\Omega$
- ③ $I_{SD} \leq -35A$, $di/dt \leq -170 A/\mu s$,
 $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^\circ C$
 Suggested $R_G = 2.35\Omega$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ $K/W = ^\circ C/W$
 $W/K = W/^\circ C$

- ⑥ **Total Dose Irradiation with V_{GS} Bias.**
 -12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019.
- ⑦ **Total Dose Irradiation with V_{DS} Bias.**
 $V_{DS} = 0.8$ rated BV_{DSS} (pre-radiation) applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019.
- ⑧ This test is performed using a flash x-ray source operated in the e-beam mode (energy ~ 2.5 MeV), 30 nsec pulse.
- ⑨ Process characterized by independent laboratory.
- ⑩ All Pre-Radiation and Post-Radiation test conditions are **identical** to facilitate direct comparison for circuit applications.

* Current is limited by Pin diameter

Case Outline and Dimensions —



CAUTION

BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

International
IR Rectifier

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